

September 2007

# MPS8598 PNP General Purpose Amplifier

- · This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA.
- · Sourced from Process 68.



1. Emitter 2. Base 3. Collector

## Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

| Symbol                            | Parameter  | Value     | Units |  |
|-----------------------------------|--|-----------|-------|--|
| $V_{CBO}$                         | Collector-Base Voltage                           | 60        | V     |  |
| $V_{CEO}$                         | Collector-Emitter Voltage                        | 60        | V     |  |
| V <sub>EBO</sub>                  | Emitter-Base Voltage                             | 5         | V     |  |
| I <sub>C</sub>                    | Collector Current (DC)                           | 100       | mA    |  |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Junction Temperature Range | -55 ~ 150 | °C    |  |

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

These ratings are based on a maximum junction temperature of 150 degrees C.

# Thermal Characteristics T<sub>a</sub>=25°C unless otherwise noted

| Symbol          | Parameter                               | Max. | Units |
|-----------------|---|------|-------|
| P <sub>D</sub>  | Total Device Dissipation                | 625  | mW    |
|                 | Derate above 25°C                       | 5.0  | mW/°C |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case    | 83.3 | °C/W  |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 200  | °C/W  |

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06".

<sup>2.</sup> These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# Electrical Characteristics $T_C=25$ °C unless otherwise noted

| Symbol                | Parameter                            | Test Condition  | Min.             | Тур. | Max.       | Units |
|-----------------------|--------------------------------------|---|------------------|------|------------|-------|
| BV <sub>CBO</sub>     | Collector-Base Voltage               | $I_{C} = 100 \mu A$   | 60               |      |            | V     |
| BV <sub>CEO</sub>     | Collector-Emitter Voltage            | I <sub>C</sub> = 10mA   | 60               |      |            | V     |
| BV <sub>EBO</sub>     | Emitter-Base Voltage                 | I <sub>E</sub> = 10μA   | 5                |      |            | V     |
| I <sub>CBO</sub>      | Collector-Base Cut-off Current       | V <sub>CB</sub> = 60V   |                  |      | 0.1        | μΑ    |
| I <sub>CEO</sub>      | Collector-Emitter Cut-off Current    | V <sub>CB</sub> = 60V   |                  |      | 0.1        | μΑ    |
| I <sub>EBO</sub>      | Emitter-Base Cut-off Current         | V <sub>EB</sub> = 4V  |                  |      | 0.1        | μΑ    |
| h <sub>FE</sub>       | DC Current Gain                      | $V_{CE} = 5V, I_{C} = 1.0mA$<br>$V_{CE} = 5V, I_{C} = 10mA$<br>$V_{CE} = 5V, I_{C} = 100mA$ | 100<br>100<br>75 |      | 300        |       |
| V <sub>CE</sub> (sat) | Collector-Emitter Saturation Voltage | $I_C = 100 \text{ mA}, I_B = 5 \text{ mA}$<br>$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$   |                  |      | 0.4<br>0.3 | V     |
| V <sub>BE</sub> (on)  | Base-Emitter On Voltage              | $V_{CE} = 5V$ , $I_{C} = 1mA$   | 0.5              |      | 0.7        | V     |
| C <sub>ob</sub>       | Output Capacitance                   | V <sub>CB</sub> = 5V, f = 1MHz  |                  |      | 8          | pF    |
| C <sub>ib</sub>       | Input Capacitance                    | V <sub>EB</sub> = 0.5V, f = 1MHz  |                  |      | 30         | pF    |
| f <sub>T</sub>        | Current gain Bandwidth Product       | $V_{CE} = 5V, I_{C} = 10mA, f = 100MHz$   | 150              |      | MHz        |       |

- NOTES:

  1. These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

  2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

  3. These ratings are based on a maximum junction temperature of 150degrees C.





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